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COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

- STMicroelectronics PREFERRED SALESTYPES
- COMPLEMENTARY PNP NPN DEVICES
- MONOLITHIC DARLINGTON CONFIGURATION
- INTEGRATED ANTIPARALLEL COLLECTOR-EMITTER DIODE

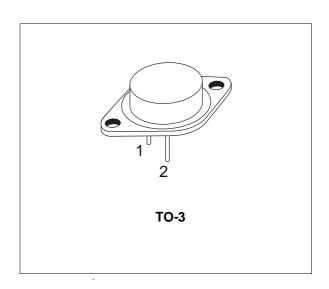
APPLICATIONS

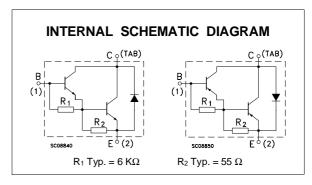
- GENERAL PURPOSE SWITCHING
- GENERAL PURPOSE AMPLIFIERS

DESCRIPTION

The MJ4035 is a silicon Epitaxial-Base NPN power transistor in monolithic Darlington configuration mounted in Jedec TO-3 metal case. It is inteded for use in general purpose and amplifier applications.

The complementary PNP type is the MJ4032.





ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | | Value | Unit | |
|------------------|--|-----|------------|------|--|
| | | PNP | MJ4032 | | |
| | | NPN | MJ4035 | | |
| V_{CBO} | Collector-Base Voltage (I _E = 0) | | 100 | V | |
| V_{CEO} | Collector-Emitter Voltage (I _B = 0) | | 100 | V | |
| V_{EBO} | Emitter-Base Voltage (I _C = 0) | | 5 | V | |
| Ic | Collector Current | | 16 | А | |
| lΒ | Base Current | | 0.5 | А | |
| P _{tot} | Total Dissipation at T _c ≤ 25 °C | | 150 | W | |
| T _{stg} | Storage Temperature | | -65 to 200 | °C | |
| Tj | Max. Operating Junction Temperature | | 200 | °C | |

For PNP types voltage and current values are negative.

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THERMAL DATA

| R _{thj-case} | Thermal Resistance Junction-case | Max | 1.17 | °C/W |
|-----------------------|----------------------------------|-----|------|------|
|-----------------------|----------------------------------|-----|------|------|

ELECTRICAL CHARACTERISTICS ($T_{case} = 25$ $^{\circ}C$ unless otherwise specified)

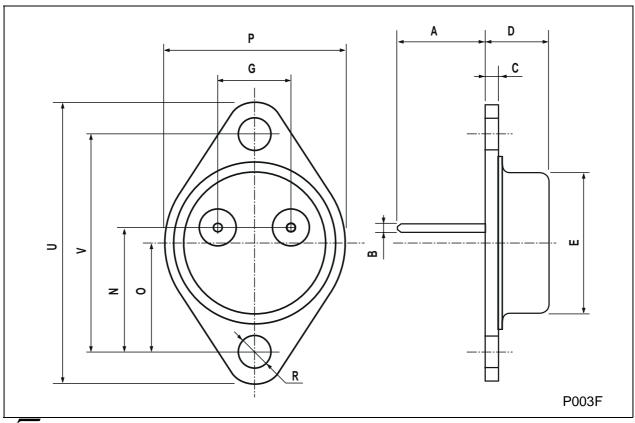
| Symbol | Parameter | Tes | t Conditions | Min. | Тур. | Max. | Unit |
|------------------------|--|--|--|------|------|----------|----------|
| I _{CER} | Collector Cut-off Current ($R_{BE} = 1K\Omega$) | V _{CE} = 100 V V _{CE} = 100 V | T _c = 150 °C | | | 1 5 | mA mA |
| I _{CEO} | Collector Cut-off Current (I _B = 0) | V _{CE} = 50 V | | | | 3 | mA |
| I _{EBO} | Emitter Cut-off Current (I _C = 0) | V _{EB} = 5 V | | | | 5 | mA |
| V _{(BR)CEO*} | Collector-Emitter Breakdown Voltage | I _C = 100 mA | | 100 | | | ٧ |
| V _{CE(sat)} * | Collector-Emitter Saturation Voltage | I _C = 10 A I _C = 16 A | I _B = 40 mA I _B = 80 mA | | | 2.5 4 | V V |
| V _{BE} * | Base-Emitter Voltage | I _C = 10 A | V _{CE} = 3 V | | | 3 | V |
| h _{FE} * | DC Current Gain | I _C = 10 A | V _{CE} = 3 V | 1000 | | | |

^{*} Pulsed: Pulse duration = 300 μs, duty cycle 1.5 % For PNP type voltage and current values are negative.

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TO-3 MECHANICAL DATA

| DIM. | mm | | | inch | | | |
|------|-------|------|-------|-------|------|-------|--|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. | |
| А | 11.00 | | 13.10 | 0.433 | | 0.516 | |
| В | 0.97 | | 1.15 | 0.038 | | 0.045 | |
| С | 1.50 | | 1.65 | 0.059 | | 0.065 | |
| D | 8.32 | | 8.92 | 0.327 | | 0.351 | |
| Е | 19.00 | | 20.00 | 0.748 | | 0.787 | |
| G | 10.70 | | 11.10 | 0.421 | | 0.437 | |
| N | 16.50 | | 17.20 | 0.649 | | 0.677 | |
| Р | 25.00 | | 26.00 | 0.984 | | 1.023 | |
| R | 4.00 | | 4.09 | 0.157 | | 0.161 | |
| U | 38.50 | | 39.30 | 1.515 | | 1.547 | |
| V | 30.00 | | 30.30 | 1.187 | | 1.193 | |



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